Degragation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons
Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Numerical analysis of the influence of deep energy level traps in SiC Schottky structures
Koel, Ants; **Rang, Toomas**; **Rang, Galina** High performance structure and materials. VI 2012 / p. 439-448 : ill

SIC schottky diode rectifier bridge represented as the diffusion-welded stack
Korolkov, Oleg; **Land, Raul**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 42

SIC schottky diode rectifier bridge represented as the diffusion-welded stack
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Land, Raul**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 697-700 : ill
https://doi.org/10.4028/www.scientific.net/MSF.897.697

Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe
Mizsei, Janos; **Korolkov, Oleg**; **Toompuu, Jana**; **Mikli, Valdek**; **Rang, Toomas** Silicon Carbide and Related Materials 2012 : selected peer reviewed papers from the 9th European Conference on Silicon Carbide and Related Materials (ECSCRM 2012), September 2-6, 2012, St. Petersburg, Russian Federation 2013 / p. 677-680 : ill

The dependence of reverse recovery time on barrier capacitance and series on-resistance in Schottky diodes
Veher, Oleksandr; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Korolkov, Oleg**; **Rang, Toomas** Materials and contact characterisation VIII 2017 / p. 15-22 : ill http://dx.doi.org/10.2495/MC170021